



ON Semiconductor®

SPICE PARAMETER

Pch MOS FET

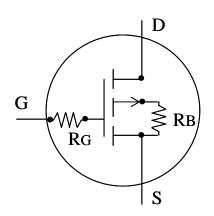
model: BSIM3V3.2

Parameter	Value	Parameter	Value	Parameter	Value
LEVEL	8				
VERSION	3.2	TNOM	27	TOX	2.7E-08
VTH0	-0.91	K1	1.96	K2	-0.04
NLX	3.20E-07	DVT0	1.12	DVT1	0.22
DVT2	-0.01	U0	300	UA	1.10E-10
UB	1.00E-21	VSAT	1.86E04	A0	0.44
AGS	1.00	A1	0	A2	1
RDSW	2.96E03	PRWG	-0.011	WR	0.83
WINT	0	LINT	2.09E-09	VOFF	-0.10
NFACTOR	1.118	CIT	0	CDSC	2.40E-04
CDSCD	0	ETA0	0.08	DSUB	0.96
PCLM	1.40	PDIBLC1	0.05	PDIBLC2	6.50E-03
DROUT	0.96	PSCBE1	1.40E09	PSCBE2	1.00E-05
PVAG	0.01	DELTA	0.10	NGATE	1.0E19
MOBMOD	1	NQSMOD	0	NOIMOD	1
CAPMOD	3	XPART	0.5	CGSO	9.00E-11
CGDO	1.50E-11	CGBO	0	CGSL	0
CGDL	3.90E-10	CKAPPA	1.20	CF	0
CLC	3.0E-09	CLE	0.8	DWC	0
DLC	1.90E-07	NOFF	3.66	VOFFCV	-0.40
ACDE	1.0	MOIN	15	CJ	2.20E-04
MJ	0.60	PB	0.41	JS	1.50E-07
NJ	1.00	XTI	3.0	IJTH	0
KT1	-0.45	UTE	-0.3	PRT	5.00E03
AT	2.5E04				

 $\begin{array}{lll} Temp = & 27 \ deg \\ L = & 1.0E\text{-}6 \ m \\ W = & 1494310E\text{-}6 \ m \\ AD = & 1494310E\text{-}12 \ m2 \end{array}$

RG = 15 ohmRB = 0.013 ohm

Date: 2007/10/29



^{*}Information herein is for example only; It is not guaranteed for volume production.